

2SA1188

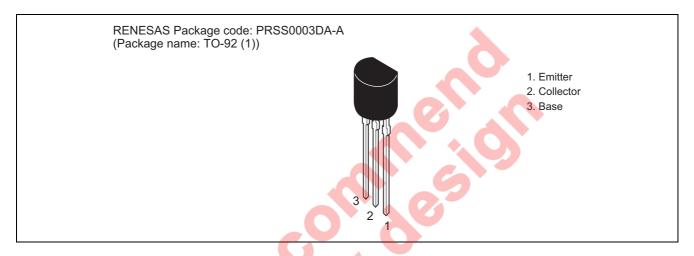
Silicon PNP Epitaxial

REJ03G0639-0300 (Previous ADE-208-1011A) Rev.3.00 Aug.10.2005

Application

Low frequency amplifier

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Rating | Unit | |
|------------------------------|----------------------|-------------|------|--|
| Collector to base voltage | V _{CBO} -90 | | V | |
| Collector to emitter voltage | V_{CEO} | -90 | V | |
| Emitter to base voltage | V_{EBO} | - 5 | V | |
| Collector current | Ic | -100 | mA | |
| Emitter current | Ι _Ε | 100 | mA | |
| Collector power dissipation | Pc | 400 | mW | |
| Junction temperature | Tj | 150 | °C | |
| Storage temperature | Tstg | -55 to +150 | °C | |

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

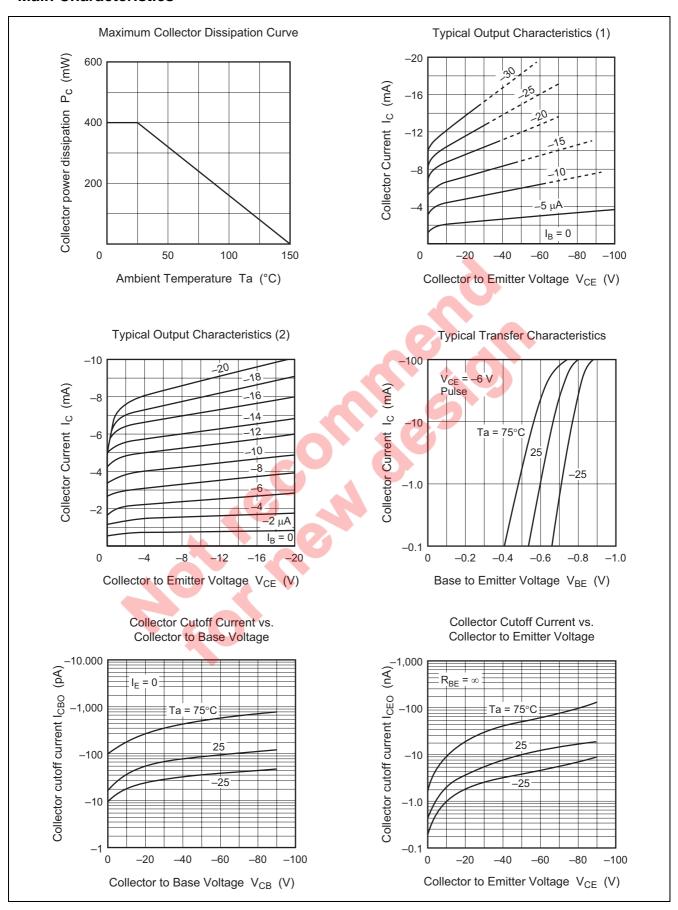
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|---|--------------------|------------|-------|-------|------|--|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | -90 | _ | _ | V | $I_C = -10 \mu A, I_E = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | -90 | _ | _ | V | $I_C = -1 \text{ mA}, R_{BE} = \infty$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | - 5 | _ | _ | V | $I_E = -10 \mu A, I_C = 0$ |
| Collector cutoff current | I _{CBO} | _ | _ | -0.1 | μΑ | $V_{CB} = -70 \text{ V}, I_E = 0$ |
| Emitter cutoff current | I _{EBO} | _ | _ | -0.1 | μΑ | $V_{EB} = -2 \text{ V}, I_{C} = 0$ |
| DC current trnsfer ratio | h _{FE} *1 | 250 | _ | 800 | | V _{CE} = −12 V, |
| | | | | | | $I_C = -2 \text{ mA}^{*2}$ |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | | -0.05 | -0.15 | V | $I_C = -10 \text{ mA},$ |
| | | | | | | $I_B = -1 \text{ mA}*^2$ |
| Base to emitter saturation voltage | $V_{BE(sat)}$ | | -0.7 | -1.0 | V | |
| Gain bandwidth product | f _T | _ | 130 | _ | MHz | $V_{CE} = -6 V$, |
| | | | | | | $I_C = -10 \text{ mA}$ |
| Collector output capacitance | Cob | _ | 3.2 | _ | pF | $V_{CB} = -10 \text{ V}, I_E = 0,$ |
| | | | | | | f = 1 MHz |

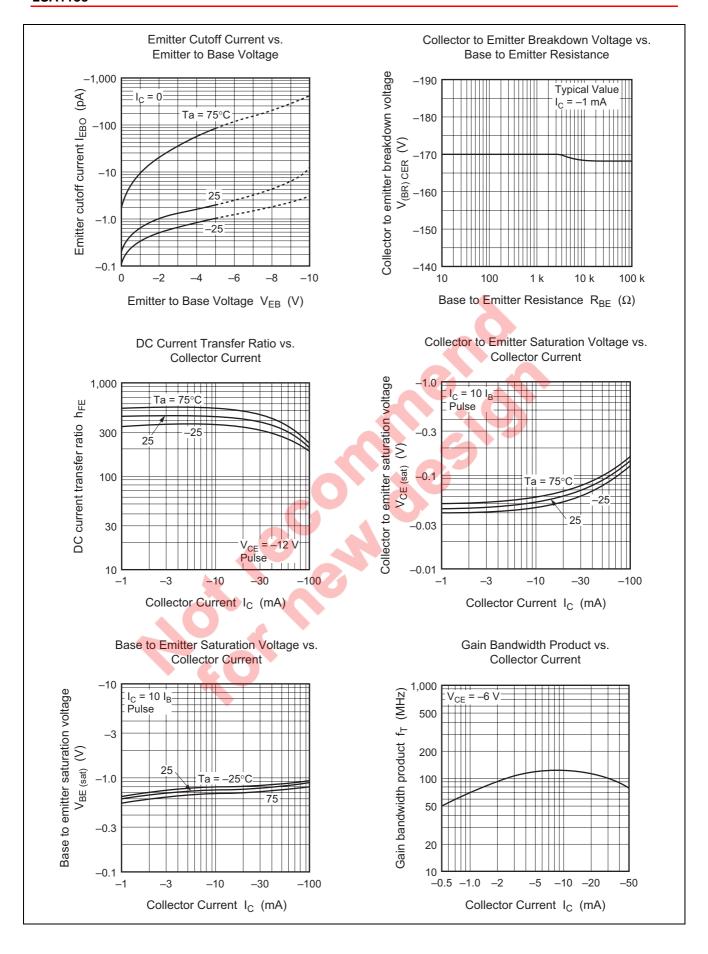
Notes: 1. The 2SA1188 is grouped by hFE as follows.

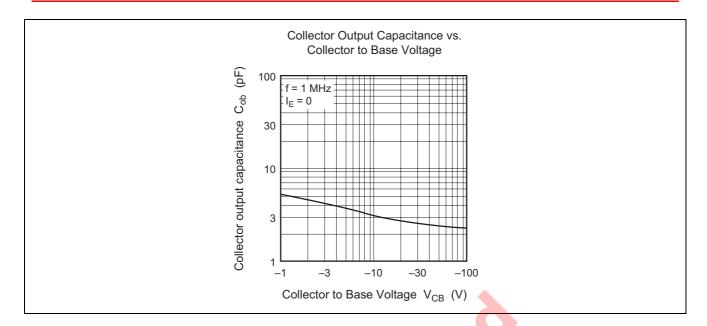
2. Pulse test

| D | E | | |
|------------|------------|--|--|
| 250 to 500 | 400 to 800 | | |

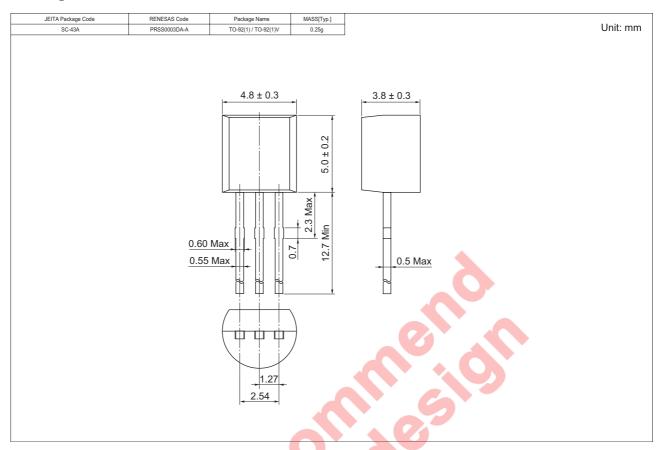
Main Characteristics







Package Dimensions



Ordering Information

| Part Name | Quantity | Shipping Container |
|--------------|----------|-------------------------|
| 2SA1188DTZ-E | 2500 | Hold Box, Radial Taping |
| 2SA1188ETZ-E | | |

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